

# NRTSV30H120CT

## Low Forward Voltage Trench-based Schottky Rectifier

### Features

- Fine Lithography Trench-based Schottky Technology for Very Low Forward Voltage and Low Leakage
- Fast Switching with Exceptional Temperature Stability
- Low Power Loss and Lower Operating Temperature
- Higher Efficiency for Achieving Regulatory Compliance
- Low Thermal Resistance
- High Surge Capability
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

### Typical Applications

- Switching Power Supplies including Notebook / Netbook Adapters, ATX and Flat Panel Display
- High Frequency and DC-DC Converters
- Freewheeling and OR-ing diodes
- Reverse Battery Protection
- Instrumentation

### Mechanical Characteristics

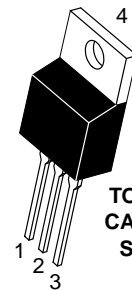
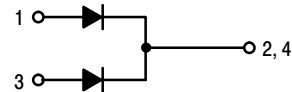
- Case: Epoxy, Molded
- Epoxy Meets Flammability Rating UL 94-0 @ 0.125 in
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Maximum for 10 sec



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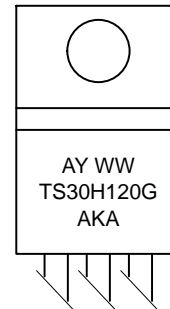
[www.onsemi.com](http://www.onsemi.com)

### PIN CONNECTIONS



TO-220AB  
CASE 221A  
STYLE 6

### MARKING DIAGRAM



TS30H120G = Specific Device Code  
A = Assembly Location  
Y = Year  
WW = Work Week  
AKA = Polarity Designator  
G = Pb-Free Package

### ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

# NRTSV30H120CT

## MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	$V_{RRM}$ $V_{RWM}$ $V_R$	120	V
Average Rectified Forward Current (Rated $V_R$ , $T_C = 124^\circ\text{C}$ ) (Rated $V_R$ , $T_C = 134^\circ\text{C}$ )	$I_{F(AV)}$ Per device Per diode	30 15	A
Peak Repetitive Forward Current (Rated $V_R$ , Square Wave, 20 kHz, $T_C = 119^\circ\text{C}$ ) (Rated $V_R$ , Square Wave, 20 kHz, $T_C = 132^\circ\text{C}$ )	$I_{FRM}$ Per device Per diode	60 30	A
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)	$I_{FSM}$	125	A
Operating Junction Temperature	$T_J$	-55 to +150	$^\circ\text{C}$
Storage Temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

## THERMAL CHARACTERISTICS

Rating	Symbol	Value	Unit
Maximum Thermal Resistance per Device (Note 1) Junction-to-Case Junction-to-Ambient	$R_{\theta JC}$ $R_{\theta JA}$	1.0 69.3	$^\circ\text{C}/\text{W}$ $^\circ\text{C}/\text{W}$

1. Assumes 150 mm<sup>2</sup> 1 oz. copper bond pad, on a FR4 board.

## ELECTRICAL CHARACTERISTICS (Per Leg unless otherwise noted)

Rating	Symbol	Typ	Max	Unit
Maximum Instantaneous Forward Voltage (Note 2) ( $I_F = 7.5\text{ A}$ , $T_J = 25^\circ\text{C}$ ) ( $I_F = 15\text{ A}$ , $T_J = 25^\circ\text{C}$ )  ( $I_F = 7.5\text{ A}$ , $T_J = 125^\circ\text{C}$ ) ( $I_F = 15\text{ A}$ , $T_J = 125^\circ\text{C}$ )	$V_F$	0.65 0.87	- 0.93	V
Maximum Instantaneous Reverse Current (Note 2) ( $V_R = 90\text{ V}$ , $T_J = 25^\circ\text{C}$ ) ( $V_R = 90\text{ V}$ , $T_J = 125^\circ\text{C}$ )  (Rated dc Voltage, $T_J = 25^\circ\text{C}$ ) (Rated dc Voltage, $T_J = 125^\circ\text{C}$ )	$I_R$	3.8 4.3	- 35	$\mu\text{A}$ mA  $\mu\text{A}$ mA
Diode Capacitance (Rated dc Voltage, $T_J = 25^\circ\text{C}$ )	$C_d$	95	-	pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

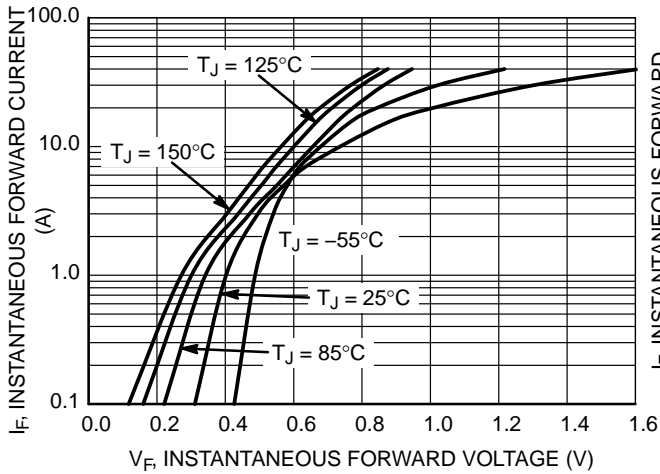
2. Pulse Test: Pulse Width = 300  $\mu\text{s}$ , Duty Cycle  $\leq 2.0\%$

## ORDERING INFORMATION

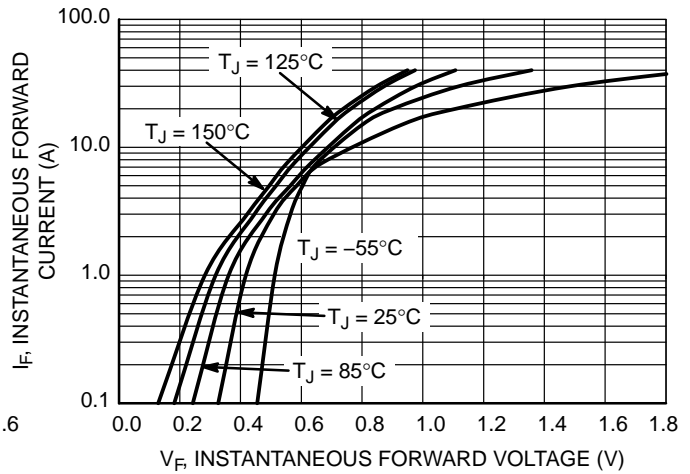
Device	Package	Shipping
NRTSV30H120CTG	TO-220AB (Pb-Free)	50 Units / Rail

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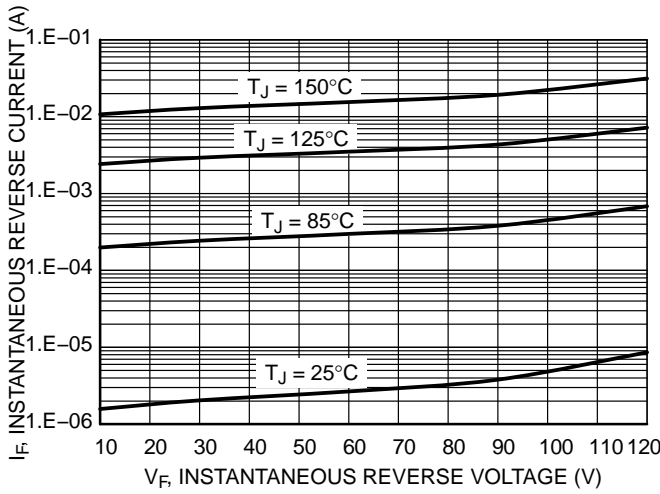
## TYPICAL CHARACTERISTICS



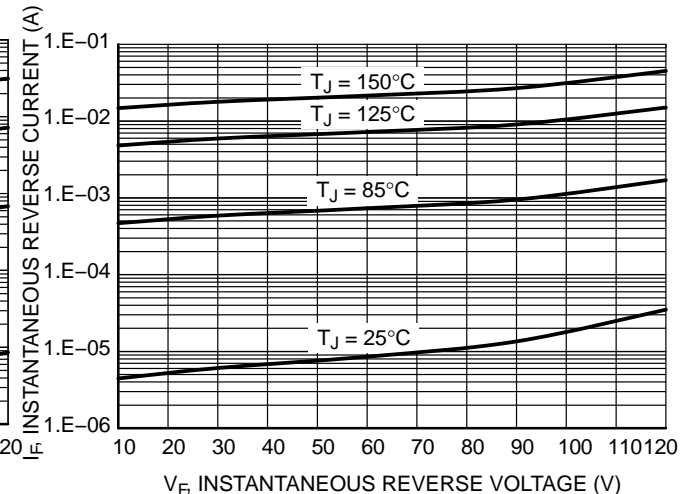
**Figure 1. Typical Instantaneous Forward Characteristics**



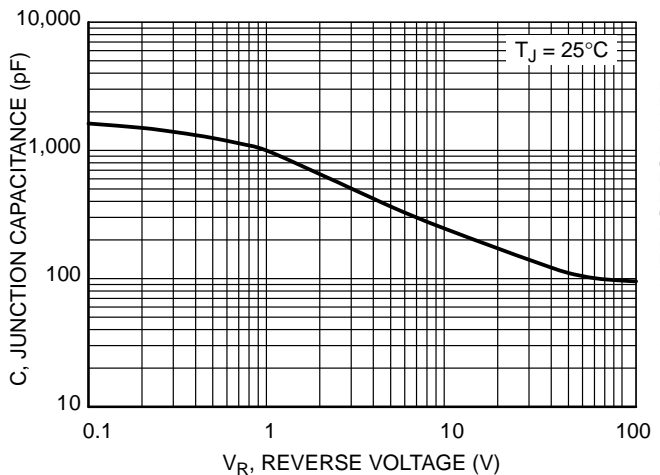
**Figure 2. Maximum Instantaneous Forward Characteristics**



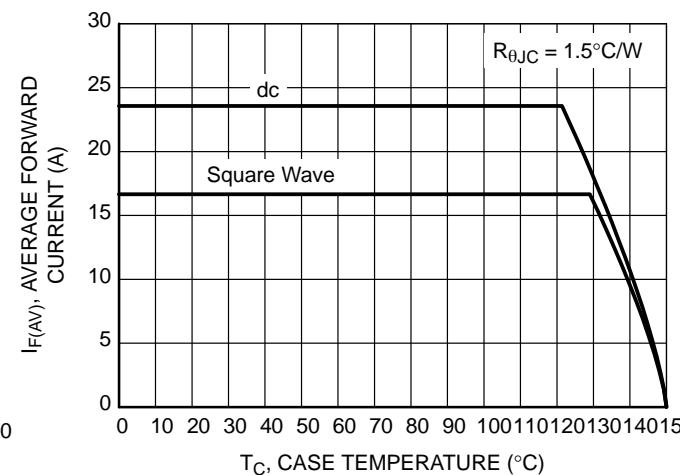
**Figure 3. Typical Reverse Characteristics**



**Figure 4. Maximum Reverse Characteristics**



**Figure 5. Typical Junction Capacitance**



**Figure 6. Current Derating per Leg**

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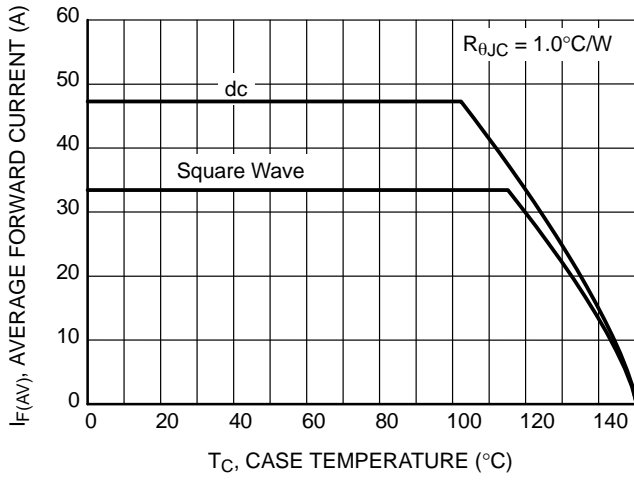


Figure 7. Current Derating, per Device

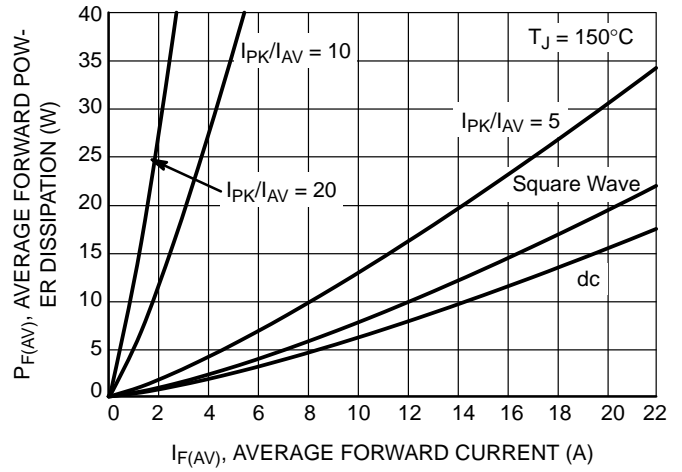


Figure 8. Forward Power Dissipation

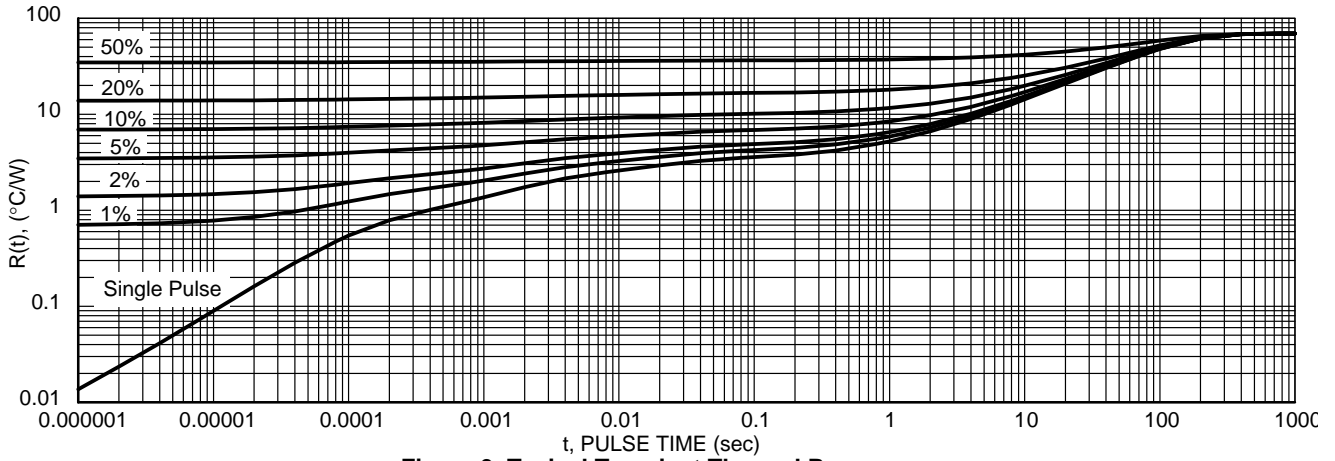


Figure 9. Typical Transient Thermal Response

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